

XN06776

Silicon P-channel MOSFET

For switching

Secondary battery pack (Li⁺ ion battery, etc.)

■ Features

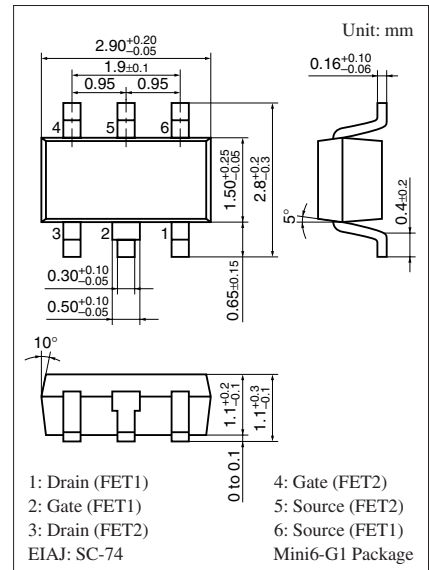
- High gate-source voltage (Drain open) V_{GSO}
- Low gate threshold voltage V_{th}
- Two elements incorporated into one package (FET)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

- 2SJ0536 × 2

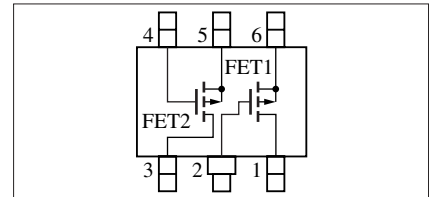
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	-50	V
Gate-source voltage (Drain open)	V_{GSO}	± 20	V
Drain current	I_D	-100	mA
Peak drain current	I_{DP}	-200	mA
Total power dissipation	P_T	300	mW
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: KA

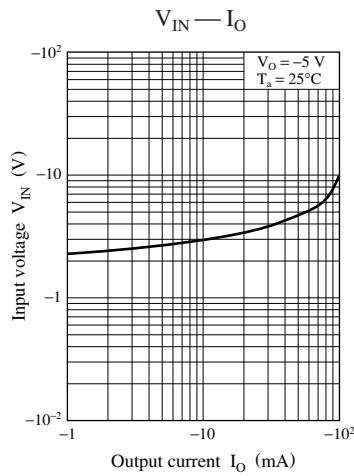
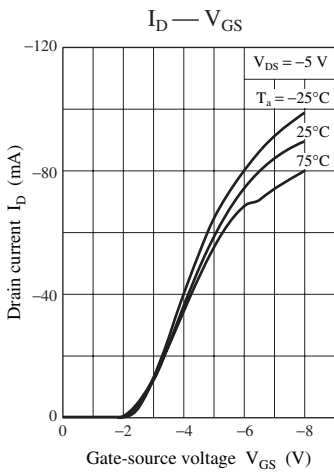
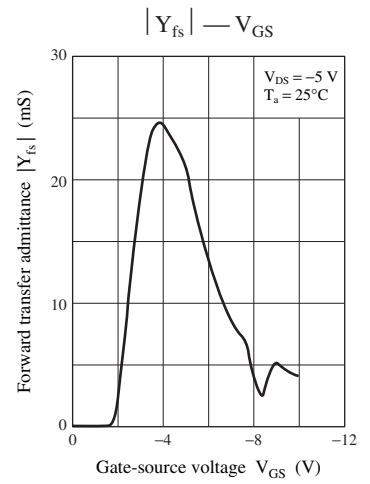
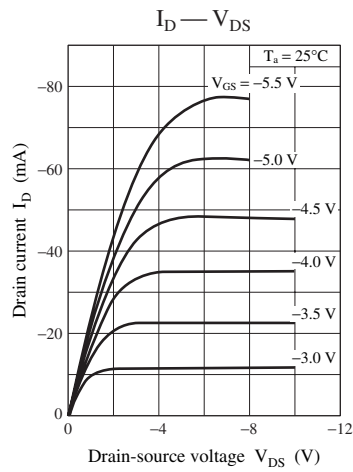
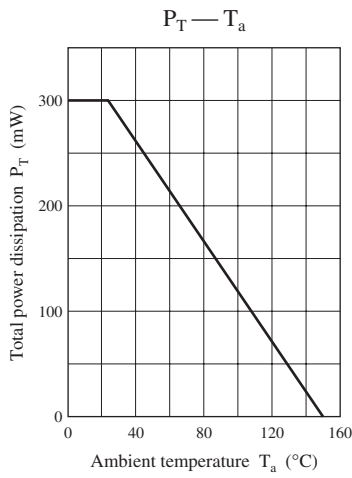
Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source cutoff current	I_{DSS}	$V_{DS} = -50\text{ V}, V_{GS} = 0\text{ V}$			-0.1	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			± 1.0	μA
Gate threshold voltage	V_{th}	$V_{DS} = -5\text{ V}, I_D = -1\ \mu\text{A}$	-1.0		-2.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -5\text{ V}, I_D = -10\text{ mA}$	10			mS
ON resistance	R_{on}	$V_{GS} = -5\text{ V}, I_D = -10\text{ mA}$		50	75	Ω
Turn-on time	t_{on}	$V_{DD} = -5\text{ V}, V_{GS} = 0\text{ V to } -5\text{ V}$ $R_L = 200\ \Omega$		100		μs
Turn-off time	t_{off}	$V_{DD} = -5\text{ V}, V_{GS} = -5\text{ V to } 0\text{ V}$ $R_L = 200\ \Omega$		25		μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.



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